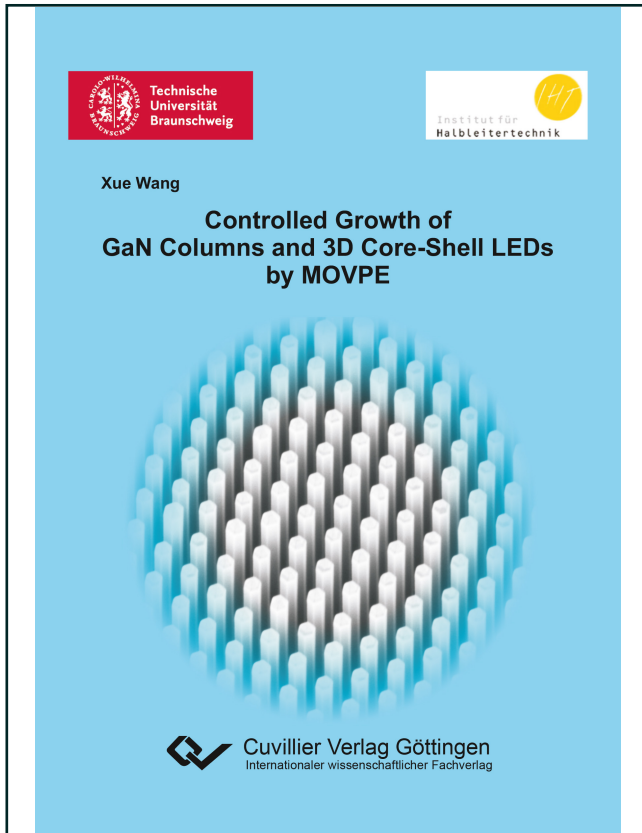




Xue Wang (Autor)

# Controlled Growth of GaN Columns and 3D Core-Shell LEDs by MOVPE



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